

ESDALC6V1P5

QUAD LOW CAPACITANCE TRANSIL™ **Application Specific Discretes** ARRAY FOR ESD PROTECTION

MAIN APPLICATIONS

Where transient overvoltage protection in ESD sensitive equipment is required, such as :

A.S.D.

- Computers
- Printers
- Communication systems and cellular phones
- Video equipment

This device is particularly adapted to the protection of symmetrical signals.

FEATURES

- 4 UNIDIRECTIONAL TRANSIL[™] FUNCTIONS.
- BREAKDOWN VOLTAGE V_{BR} = 6.1V MIN.
- LOW DIODE CAPACITANCE (12pF @ 0V)
- LOW LEAKAGE CURRENT < 100 nA</p>
- VERY SMALL PCB AREA < 2.6 mm²

DESCRIPTION

The ESDALC6V1P5 is a monolithic array designed to protect up to 4 lines against ESD transients.

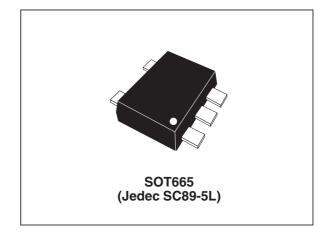
This device is ideal for applications where both reduced line capacitance and board space saving are required.

BENEFITS

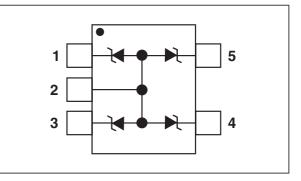
- High ESD protection level.
- High integration.
- Suitable for high density boards.

COMPLIES WITH THE FOLLOWING STANDARDS:

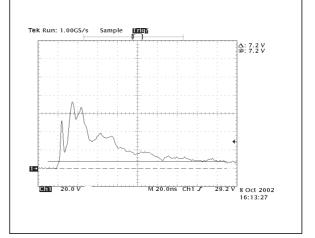
- IEC61000-4-2 level 4: 15 kV (air discharge) 8 kV (contact discharge)
- MIL STD 883E-Method 3015-7: class 3 25kV HBM (Human Body Model)



FUNCTIONAL DIAGRAM



ESD response to IEC61000-4-2 level 4 (15kV contact)



February 2004 - Ed: 1

ESDALC6V1P5

ABSOLUTE RATINGS ($T_{amb} = 25^{\circ}C$)

Symbol	Parameter	Test conditions	Value	Unit
V _{PP}	ESD discharge - IEC61000-4 IEC61000-4	± 15 ± 8	kV	
P _{PP}	Peak pulse power (8/20 µs) (30	W	
Tj	Junction temperature	125	°C	
T _{stg}	Storage temperature range	- 55 to + 150	°C	
TL	Maximum lead temperature fo	260	°C	
T _{op}	Operating temperature range	- 40 to + 125	°C	

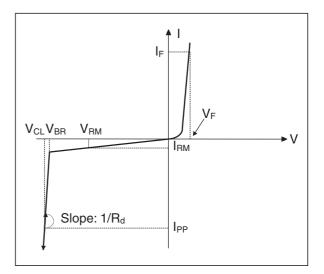
Note 1: for a surge greater than the maximum values, the diode will fail in short-circuit.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient on printed circuit on recommended pad layout	220	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter
V _{RM}	Stand-off voltage
V _{BR}	Breakdown voltage
V _{CL}	Clamping voltage
I _{RM}	Leakage current
I _{PP}	Peak pulse current
αΤ	Voltage tempature coefficient
VF	Forward voltage drop
С	Capacitance per line
R _d	Dynamic resistance



	V	BR @	I _R	I _{RM} @	V _{RM}	Rd	αΤ	С
Types	min.	max.		max.		typ.	max.	typ.
Types								@ 0V
	V	V	mA	μA	V	Ω	10 ⁻⁴ /°C	pF
ESDALC6V1P5	6.1	7.2	1	0.1	3	1.5	4.5	12

Fig. 1: Relative variation of peak pulse power versus initial junction temperature.

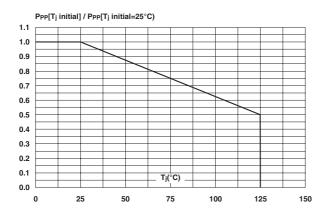


Fig. 2: Peak pulse power versus exponential pulse duration.

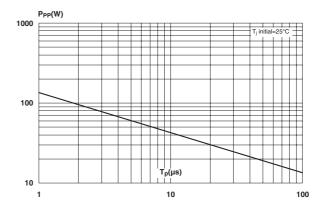


Fig. 3: Clamping voltage versus peak pulse current (typical values, rectangular waveform).

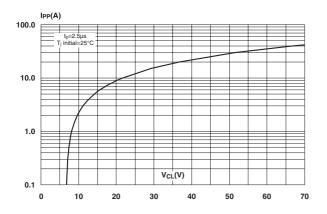
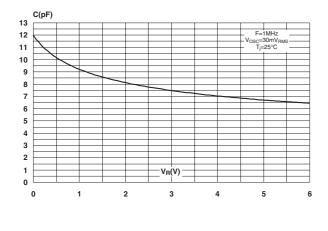


Fig. 5: Junction capacitance versus reverse voltage applied (typical values).



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Fig. 4: Forward voltage drop versus peak forward current (typical values).

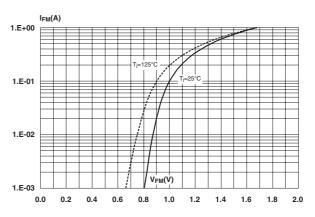
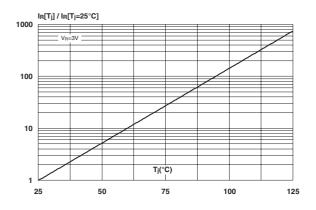
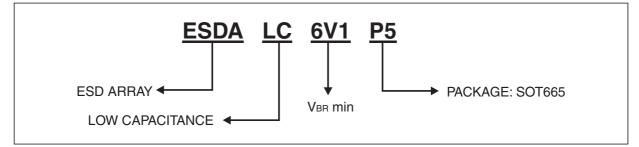


Fig. 6: Relative variation of leakage current versus junction temperature (typical values).



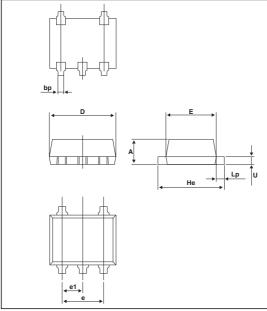
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ORDER CODE



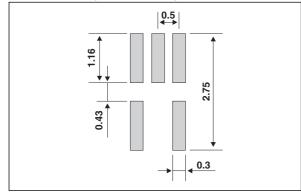
Ordering type	Marking	Package	Weight	Base qty	Delivery mode
ESDALC6V1P5	A1	SOT665	2.9 mg.	3000	Tape & reel

PACKAGE MECHANICAL DATA SOT-665

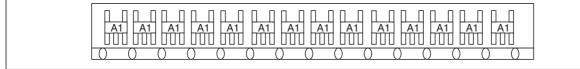


	DIMENSIONS					
REF.	Millim	neters	Inches			
	Min.	Max.	Min.	Max.		
А	0.50	0.60	0.020	0.024		
bp	0.17	0.27	0.007	0.011		
С	0.08	0.18	0.003	0.007		
D	1.50	1.70	0.060	0.067		
Е	1.10	1.30	0.043	0.051		
е	1.00		0.040			
e1	0.50		0.020			
He	1.50	1.70	0.059	0.067		
Lp	0.10	0.30	0.004	0.012		

FOOT PRINT (in millimeters)



REEL ORIENTATION



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